

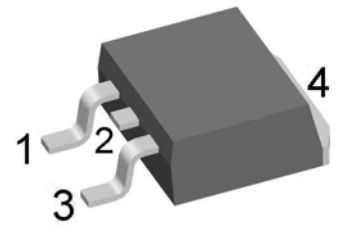
HiPerFRED²

| | | |
|-----------|---|------|
| V_{RRM} | = | 300V |
| I_{FAV} | = | 60A |
| t_{rr} | = | 35ns |

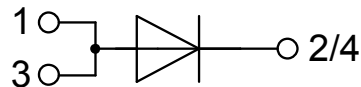
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DPG60IM300PC



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak)

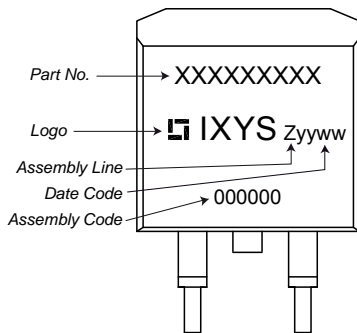
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

| Fast Diode | | | | Ratings | | |
|------------|--|---|-------------------------|---------|------|------------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| V_{RSM} | max. non-repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 300 | V |
| V_{RRM} | max. repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 300 | V |
| I_R | reverse current, drain current | $V_R = 300 V$ | $T_{VJ} = 25^{\circ}C$ | | 1 | μA |
| | | $V_R = 300 V$ | $T_{VJ} = 150^{\circ}C$ | | 0.35 | mA |
| V_F | forward voltage drop | $I_F = 60 A$ | $T_{VJ} = 25^{\circ}C$ | | 1.43 | V |
| | | | | | 1.78 | V |
| | | $I_F = 60 A$ | $T_{VJ} = 150^{\circ}C$ | | 1.14 | V |
| | | | | | 1.53 | V |
| I_{FAV} | average forward current | $T_C = 135^{\circ}C$ rectangular $d = 0.5$ | $T_{VJ} = 175^{\circ}C$ | | 60 | A |
| | | | | | | |
| V_{FO} | threshold voltage | } for power loss calculation only | $T_{VJ} = 175^{\circ}C$ | | 0.69 | V |
| r_F | slope resistance | | | | 6.4 | m Ω |
| R_{thJC} | thermal resistance junction to case | | | | 0.45 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | 0.25 | | K/W |
| P_{tot} | total power dissipation | $T_C = 25^{\circ}C$ | | | 335 | W |
| I_{FSM} | max. forward surge current | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 V$ | $T_{VJ} = 45^{\circ}C$ | | 550 | A |
| C_J | junction capacitance | $V_R = 150 V \quad f = 1 \text{ MHz}$ | $T_{VJ} = 25^{\circ}C$ | | 80 | pF |
| I_{RM} | max. reverse recovery current | } $I_F = 60 A; V_R = 200 V$ | $T_{VJ} = 25^{\circ}C$ | | 3.5 | A |
| | | | $T_{VJ} = 125^{\circ}C$ | | 9 | A |
| t_{rr} | reverse recovery time | } $-di_F/dt = 200 A/\mu s$ | $T_{VJ} = 25^{\circ}C$ | | 35 | ns |
| | | | $T_{VJ} = 125^{\circ}C$ | | 65 | ns |

| Package TO-263 (D2Pak) | | | Ratings | | | |
|------------------------|------------------------------|----------------------------|---------|------|------|------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal ¹⁾ | | | 35 | A |
| T_{VJ} | virtual junction temperature | | -55 | | 175 | °C |
| T_{op} | operation temperature | | -55 | | 150 | °C |
| T_{stg} | storage temperature | | -55 | | 150 | °C |
| Weight | | | | 2 | | g |
| F_C | mounting force with clip | | 20 | | 60 | N |

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 60 = Current Rating [A]
- IM = Single Diode
- 300 = Reverse Voltage [V]
- PC = TO-263AB (D2Pak) (2)

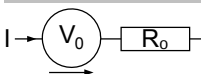
| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|--------------|--------------------|---------------|----------|----------|
| Standard | DPG60IM300PC | DPG60IM300PC | Tape & Reel | 800 | 502404 |

| Similar Part | Package | Voltage class |
|--------------|--------------|---------------|
| DPG60I300HA | TO-247AD (2) | 300 |

Equivalent Circuits for Simulation

* on die level

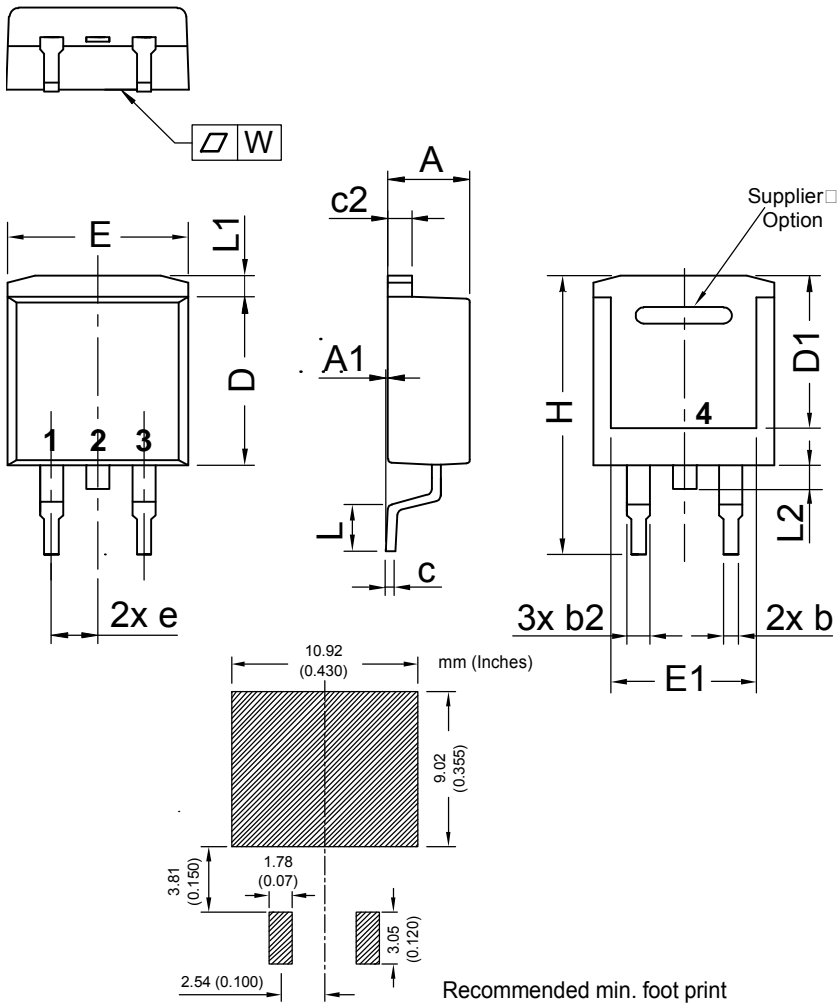
$T_{VJ} = 175\text{ °C}$



Fast Diode

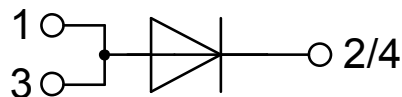
| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.69 | V |
| $R_{0\ max}$ | slope resistance * | 3.2 | mΩ |

Outlines TO-263 (D2Pak)



| Dim. | Millimeter | | Inches | |
|------|------------|-------|-------------|-------|
| | min | max | min | max |
| A | 4.06 | 4.83 | 0.160 | 0.190 |
| A1 | typ. 0.10 | | typ. 0.004 | |
| A2 | 2.41 | | 0.095 | |
| b | 0.51 | 0.99 | 0.020 | 0.039 |
| b2 | 1.14 | 1.40 | 0.045 | 0.055 |
| c | 0.40 | 0.74 | 0.016 | 0.029 |
| c2 | 1.14 | 1.40 | 0.045 | 0.055 |
| D | 8.38 | 9.40 | 0.330 | 0.370 |
| D1 | 8.00 | 8.89 | 0.315 | 0.350 |
| D2 | 2.5 | | 0.098 | |
| E | 9.65 | 10.41 | 0.380 | 0.410 |
| E1 | 6.22 | 8.50 | 0.245 | 0.335 |
| e | 2.54 BSC | | 0.100 BSC | |
| e1 | 4.28 | | 0.169 | |
| H | 14.61 | 15.88 | 0.575 | 0.625 |
| L | 1.78 | 2.79 | 0.070 | 0.110 |
| L1 | 1.02 | 1.68 | 0.040 | 0.066 |
| W | typ. 0.02 | 0.040 | typ. 0.0008 | 0.002 |

All dimensions conform with and/or within JEDEC standard.



Fast Diode

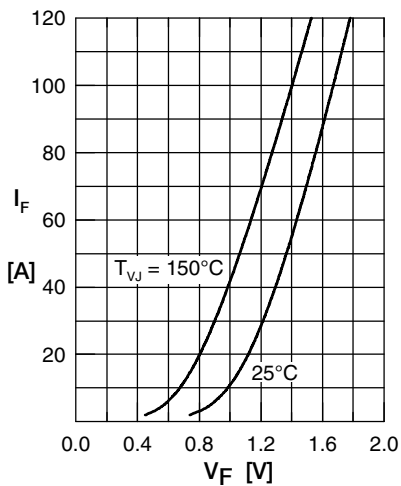


Fig. 1 Forward current I_F versus V_F

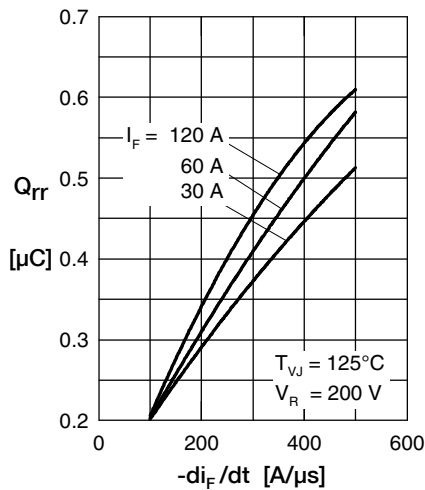


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

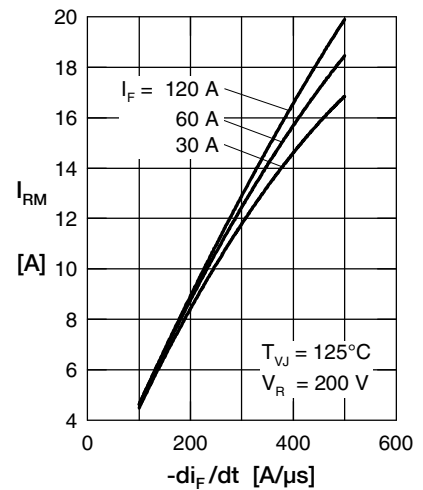


Fig. 3 Typ. reverse recovery current I_{RM} versus $-di_F/dt$

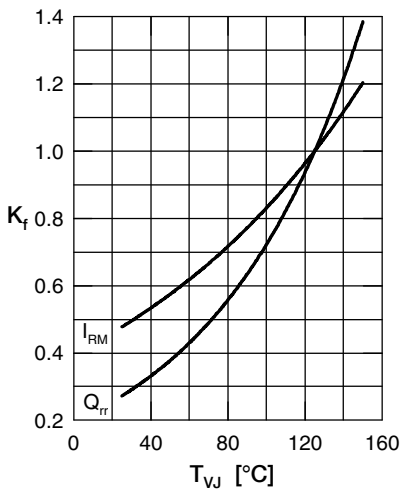


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

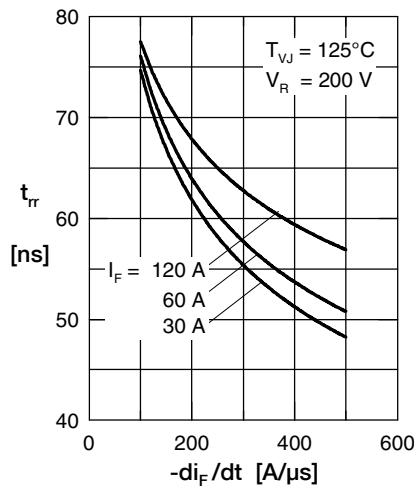


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

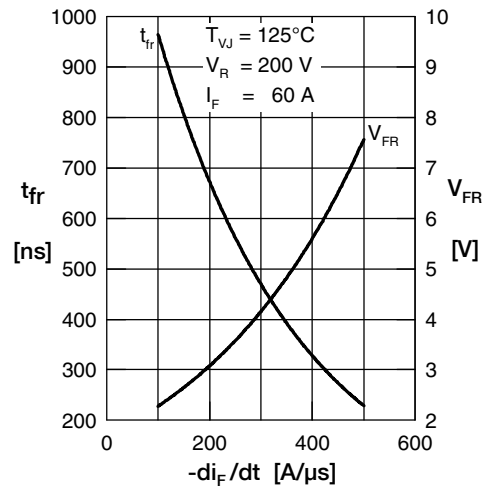


Fig. 6 Typ. forward recovery voltage V_{FR} & time t_{fr} versus di_F/dt

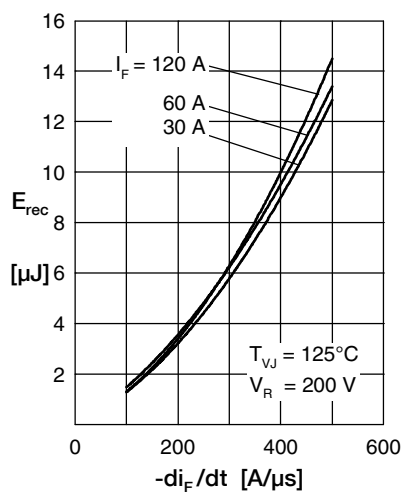


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

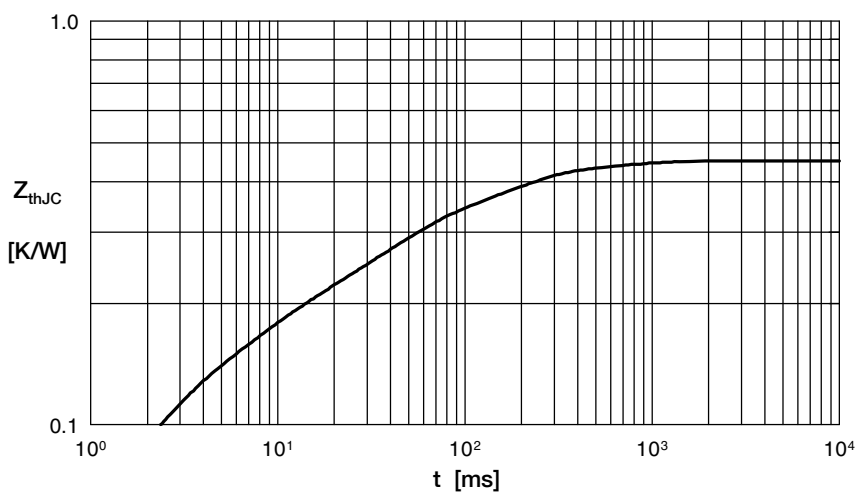


Fig. 8 Transient thermal impedance junction to case